



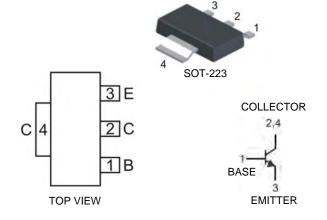
NPN SURFACE MOUNT TRANSIS

Features

- **Epitaxial Planar Die Construction**
- Complementary PNP Type Available (DZT953)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

Mechanical Data

- Case: SOT-223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Copper Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.115 grams (approximate)



Schematic and Pin Configuration

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	200	V
Collector-Emitter Voltage	V _{CEO}	100	V
Emitter-Base Voltage	V_{EBO}	6	V
Continuous Collector Current	Ic	6	Α
Power Dissipation	P _{tot}	1 (Note 3) 3 (Note 4)	W
Operating and Storage Temperature Range	T_j, T_{STG}	-55 to +150	°C

Notes:

- No purposefully added lead. 1.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php. Device mounted on FR-4 PCB, pad layout as shown on page 4.
- The power which can be dissipated, assuming the device is mounted in a typical manner on a PCB with copper equal to 4 square inch minimum.

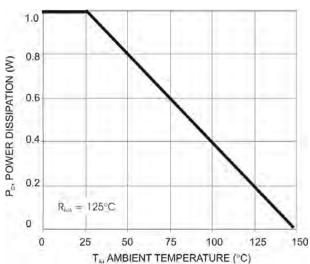


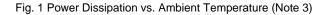
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS								
Collector-Base Breakdown Voltage	V _{(BR)CBO}	200		_	V	$I_C = 100 \mu A, I_E = 0$		
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	100		_	V	$I_C = 10 \text{mA*}, I_B = 0$		
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6			V	$I_E = 100 \mu A, I_C = 0$		
Collector Cutoff Current	I _{CBO}	_		10 1	nA μA	$V_{CB} = 150V, I_{E} = 0$ $V_{CB} = 150V, I_{E} = 0, T_{A} = 100^{\circ}C$		
Emitter Cutoff Current	I _{EBO}	_	_	10	nA	$V_{EB} = 6V, I_{C} = 0$		
ON CHARACTERISTICS								
Collector-Emitter Saturation Voltage	V _{CE(SAT)}			50 150 340	mV	I _C = 0.1A, I _B = 5mA* I _C = 2A, I _B = 100mA* I _C = 5A, I _B = 500mA*		
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	_	_	1250	mV	$I_C = 5A$, $I_B = 500mA^*$		
Base-Emitter Turn-On Voltage	$V_{BE(ON)}$	_	_	1100	mV	$I_{CE} = 5A, V_{CE} = 2V^*$		
DC Current Gain	h _{FE}	100 100 50 20		300 — —		$\begin{split} I_{C} &= 10 \text{mA}, \ V_{CE} = 2 \text{V}^{*} \\ I_{C} &= 2 \text{A}, \ V_{CE} = 2 \text{V}^{*} \\ I_{C} &= 4 \text{A}, \ V_{CE} = 2 \text{V}^{*} \\ I_{C} &= 10 \text{A}, \ V_{CE} = 2 \text{V}^{*} \end{split}$		
SMALL SIGNAL CHARACTERISTICS								
Current Gain-Bandwidth Product	f⊤	_	130	_	MHz	I _C = 100mA, V _{CE} = 10V, f = 50MHz		
Output Capacitance	C_{obo}		35	_	pF	V _{CB} = 10V, f = 1MHz		
SWITCHING CHARACTERISTICS								
Switching Times	t _{on} t _{off}	_	50 1650	_	ns ns	$I_C = 1A$, $V_{CC} = 10V$ $I_{B1} = I_{B2} = 100mA$		

Measured under pulsed conditions. Pulse width = $300\mu s$. Duty cycle $\leq 2\%$

Typical Characteristics @T_{amb} = 25°C unless otherwise specified





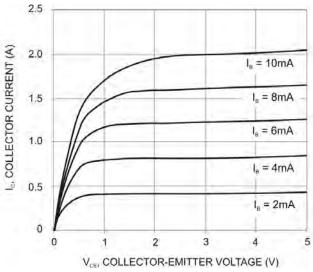


Fig. 2 Collector Current vs. Collector Emitter-Voltage

3. Device mounted on FR-4 PCB, pad layout as shown on page 4.



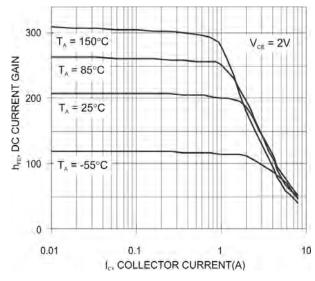


Fig. 3 Typical DC Current Gain vs. Collector Current

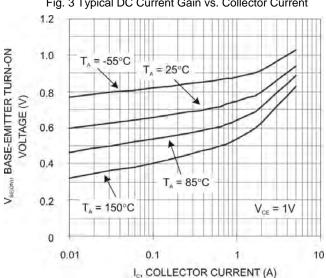


Fig. 5 Base-Emitter Turn-On Voltage vs. Collector Current

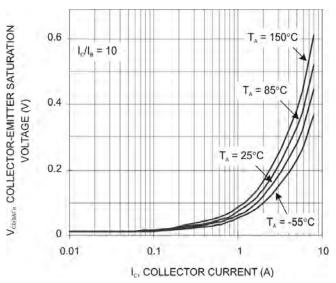


Fig. 4 Collector-Emitter Saturation Voltage vs. Collector Current

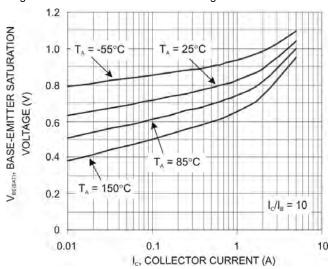


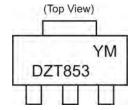
Fig. 6 Base-Emitter Saturation Voltage vs. Collector Current

Ordering Information (Note 5)

Device	Packaging	Shipping
DZT853-13	SOT-223	2500/Tape & Reel

5. Packaging Details as shown on page 4, or go to our website at http://www.diodes.com/ap2007.pdf.

Marking Information



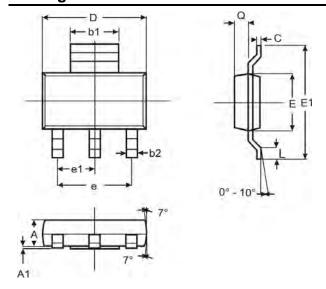
DZT853 = Product Type Marking Code YM = Date Code Marking Y = Year ex: T = 2006 M = Month ex: 9 = September

Date Code Key

Date Code Ney												
Year	200	6	2007		2008	20	09	2010		2011	2	2012
Code	Т		U		V	V	٧	Х		Υ		Z
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

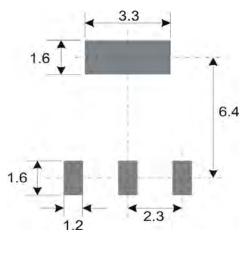


Package Outline Dimensions



SOT-223							
Dim	Min	Max	Тур				
Α	1.55	1.65	1.60				
A 1	0.010	0.15	0.05				
b1	2.90	3.10	3.00				
b2	0.60	0.80	0.70				
С	0.20	0.30	0.25				
D	6.45	6.55	6.50				
Е	3.45	3.55	3.50				
E1	6.90	7.10	7.00				
е	_	_	4.60				
e1	_	_	2.30				
L	0.85	1.05	0.95				
Q	0.84	0.94	0.89				
All Dimensions in mm							

Suggested Pad Layout: (Based on IPC-SM-782)



(Unit:mm)

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